

Abstract

In a semiconductor memory device provided with a redundancy circuit for conducting a repair of defective memory cells, the memory cell defects which
5 are unevenly distributed can be efficiently repaired.

The semiconductor memory device has a plurality of memory blocks, and the memory block includes a plurality of segments. A redundancy memory block which substitutes for defective data of
10 a segment is physically provided to each of the plurality of memory blocks. A block address of the redundancy memory block is logically allocated to the plurality of memory blocks in common.